



# SILICON POWER MOS FET

# NE5500234

## 4.8 V N-CHANNEL SILICON POWER MOS FET POWER AMPLIFIER FOR DCS1800/PCS1900 HANDSETS

### DESCRIPTION

The NE5500234 is an N-channel silicon power MOS FET specially designed as the transmission power amplifier for DCS1800 and PCS1900 handsets. Die are manufactured using our NEWMOS technology (our 0.6  $\mu\text{m}$  WSi gate lateral MOS FET), housed in a surface mount 3-pin power Minimold (34 PKG) (SOT-89 type) package. The device can deliver 32.5 dBm output power with 50% power added efficiency at 1.9 GHz with 4.8 V supply voltage.

### FEATURES

- High output power :  $P_{\text{out}} = 32.5 \text{ dBm TYP.}$  ( $V_{\text{DS}} = 4.8 \text{ V}$ ,  $I_{\text{Dset}} = 400 \text{ mA}$ ,  $f = 1.9 \text{ GHz}$ ,  $P_{\text{in}} = 25 \text{ dBm}$ )
- High power added efficiency :  $\eta_{\text{add}} = 50\% \text{ TYP.}$  ( $V_{\text{DS}} = 4.8 \text{ V}$ ,  $I_{\text{Dset}} = 400 \text{ mA}$ ,  $f = 1.9 \text{ GHz}$ ,  $P_{\text{in}} = 25 \text{ dBm}$ )
- High linear gain :  $G_{\text{L}} = 11 \text{ dB TYP.}$  ( $V_{\text{DS}} = 4.8 \text{ V}$ ,  $I_{\text{Dset}} = 400 \text{ mA}$ ,  $f = 1.9 \text{ GHz}$ )
- Surface mount package : 3-pin power Minimold (34 PKG) (SOT-89 type)
- Single supply :  $V_{\text{DS}} = 3.0 \text{ to } 6.0 \text{ V}$

### APPLICATIONS

- Digital cellular phones : DCS1800/PCS1900 handsets
- <R> • Handheld transceiver : FRS (Family Radio Service), GMRS (General Mobile Radio Service)
- Others : General purpose amplifiers for various applications

### <R> ORDERING INFORMATION

| Part Number  | Order Number    | Package  | Marking | Supplying Form  |
|--------------|-----------------|--|---------|---|
| NE5500234    | NE5500234-AZ    | 3-pin power minimold<br>(SOT-89, Our code: 34)<br>(Pb-Free : External<br>solder plating) | V2      | • Magazine case<br>• Qty 25 pcs/case  |
| NE5500234-T1 | NE5500234-T1-AZ | 3-pin power minimold<br>(SOT-89, Our code: 34)<br>(Pb-Free : External<br>solder plating) |         | • 12 mm wide embossed taping<br>• Source pin face the perforation side of the tape<br>• Qty 1 kpcs/reel |

**Remarks 1.** To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE5500234-AZ

**2.** This product is containing Pb-material inside.

**Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge**

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = +25°C)**

Operation in excess of any one of these parameters may result in permanent damage.

| Parameter               | Symbol           | Ratings     | Unit |
|-------------------------|------------------|-------------|------|
| Drain to Source Voltage | V <sub>DS</sub>  | 20          | V    |
| Gate to Source Voltage  | V <sub>GS</sub>  | 6.0         | V    |
| Drain Current           | I <sub>D</sub>   | 1.0         | A    |
| Total Power Dissipation | P <sub>tot</sub> | 10          | W    |
| Channel Temperature     | T <sub>ch</sub>  | 125         | °C   |
| Storage Temperature     | T <sub>stg</sub> | -65 to +125 | °C   |

**RECOMMENDED OPERATING CONDITIONS**

| Parameter               | Symbol          | Test Conditions                         | MIN. | TYP. | MAX. | Unit |
|-------------------------|-----------------|---|------|------|------|------|
| Drain to Source Voltage | V <sub>DS</sub> |   | 3.0  | 4.8  | 6.0  | V    |
| Gate to Source Voltage  | V <sub>GS</sub> |   | 0    | 2.0  | 3.5  | V    |
| Drain Current           | I <sub>D</sub>  | Duty Cycle ≤ 50%, T <sub>on</sub> ≤ 1 s | -    | 0.75 | 1.0  | A    |
| Input Power             | P <sub>in</sub> | f = 1.9 GHz, V <sub>DS</sub> = 4.8 V    | -    | -    | 27   | dBm  |

**ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = +25°C, unless otherwise specified, using our standard test fixture.)

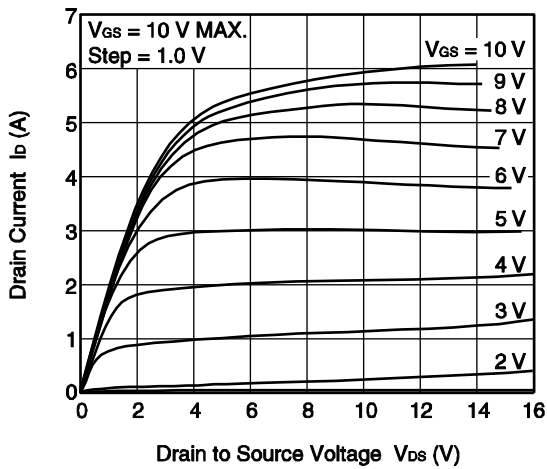
| Parameter  | Symbol            | Test Conditions                                   | MIN. | TYP. | MAX. | Unit |
|--|-------------------|---|------|------|------|------|
| Gate to Source Leakage Current                                       | I <sub>GSS</sub>  | V <sub>GS</sub> = 6.0 V                           | -    | -    | 100  | nA   |
| Drain to Source Leakage Current<br>(Zero Gate Voltage Drain Current) | I <sub>DSS</sub>  | V <sub>DS</sub> = 8.5 V                           | -    | -    | 100  | nA   |
| Gate Threshold Voltage   | V <sub>th</sub>   | V <sub>DS</sub> = 4.8 V, I <sub>DS</sub> = 1 mA   | 1.0  | 1.4  | 2.0  | V    |
| Thermal Resistance   | R <sub>th</sub>   | Channel to Case                                   | -    | 10   | -    | °C/W |
| Transconductance   | g <sub>m</sub>    | V <sub>DS</sub> = 4.8 V, I <sub>DS</sub> = 500 mA | -    | 840  | -    | mS   |
| Drain to Source Breakdown Voltage                                    | BV <sub>DSS</sub> | I <sub>DSS</sub> = 10 μA                          | 20   | 24   | -    | V    |
| Output Power   | P <sub>out</sub>  | f = 1.9 GHz, V <sub>DS</sub> = 4.8 V,             | 31.5 | 32.5 | -    | dBm  |
| Drain Current  | I <sub>D</sub>    | P <sub>in</sub> = 25 dBm,                         | -    | 610  | -    | mA   |
| Power Added Efficiency   | η <sub>add</sub>  | I <sub>Dset</sub> = 400 mA (RF OFF)               | 43   | 50   | -    | %    |
| Linear Gain <sup>Note</sup>  | G <sub>L</sub>    |   | -    | 11.0 | -    | dB   |

**Note** P<sub>in</sub> = 10 dBm

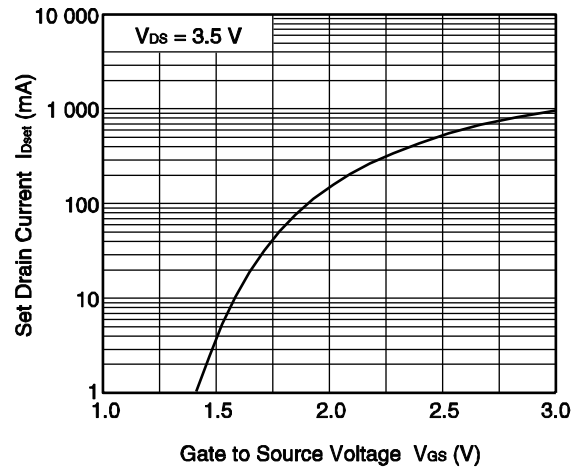
DC performance is 100% testing. RF performance is testing several samples per wafer.  
Wafer rejection criteria for standard devices is 1 reject for several samples.

<R> TYPICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)

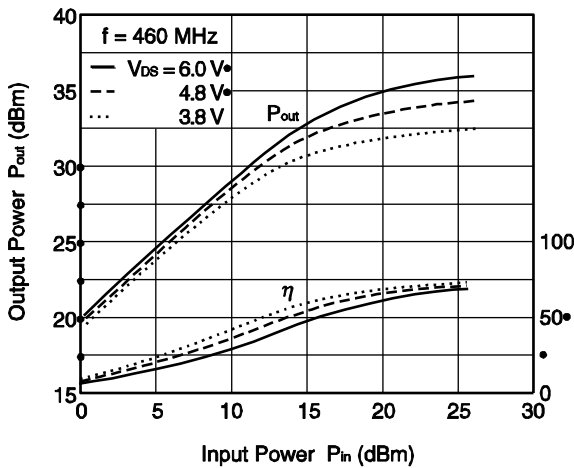
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



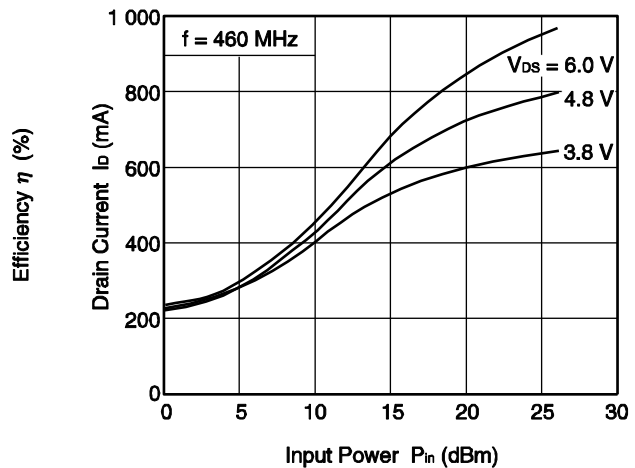
SET DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



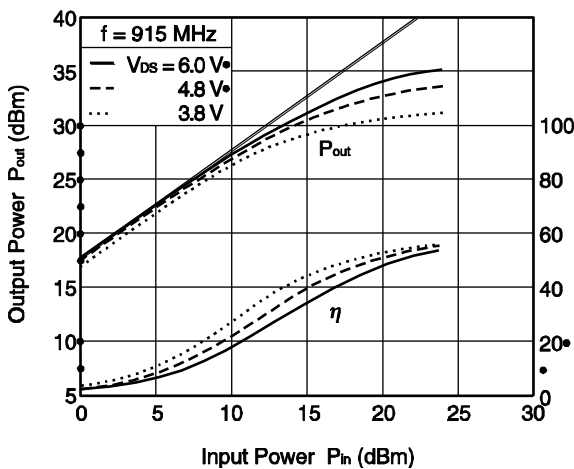
OUTPUT POWER, EFFICIENCY vs. INPUT POWER



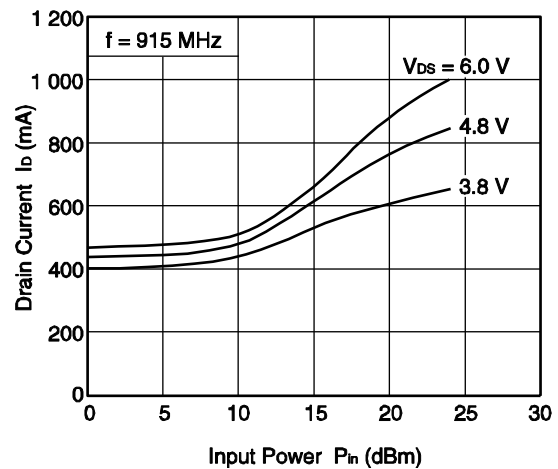
DRAIN CURRENT vs. INPUT POWER



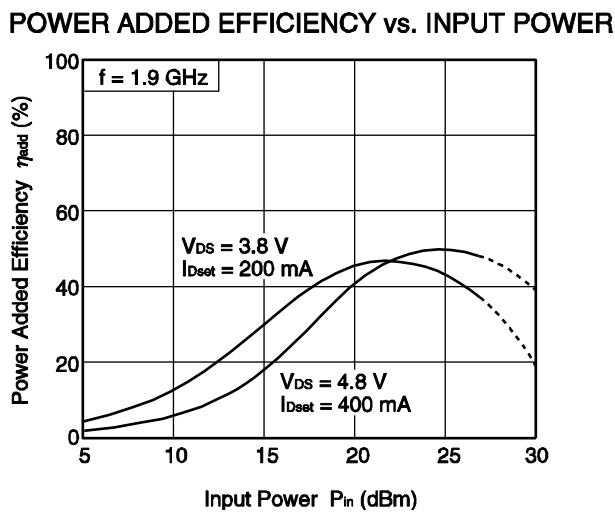
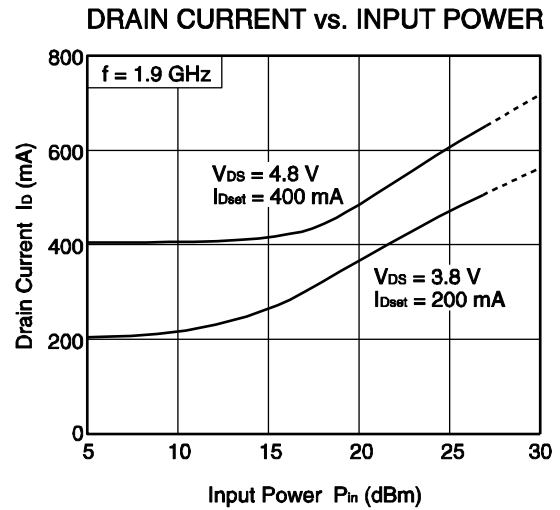
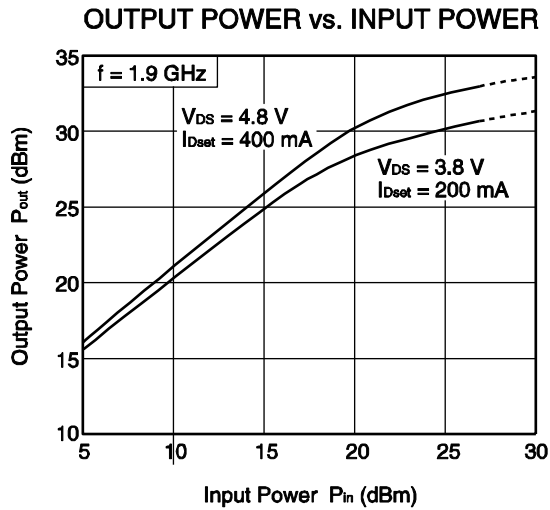
OUTPUT POWER, EFFICIENCY vs. INPUT POWER



DRAIN CURRENT vs. INPUT POWER



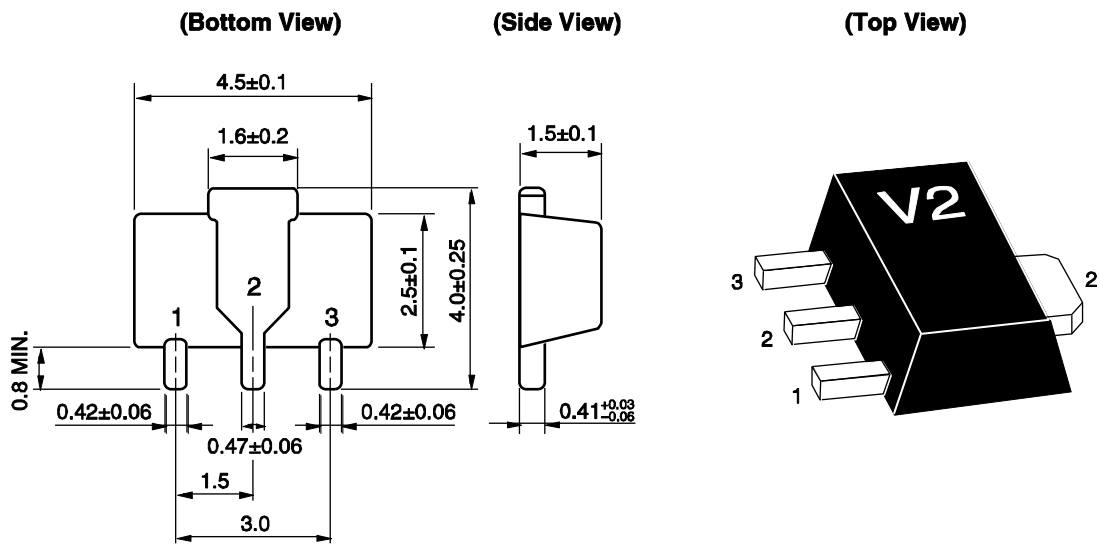
Remark The graphs indicate nominal characteristics.



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**PACKAGE DIMENSIONS**

**3-PIN POWER MINIMOLD (34 PKG) (UNIT: mm)**



**PIN CONNECTIONS**

- 1. Drain
- 2. Source
- 3. Gate

<R> **RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

| Soldering Method | Soldering Conditions  | Condition Symbol |
|------------------|---|------------------|
| Infrared Reflow  | Peak temperature (package surface temperature) : 260°C or below<br>Time at peak temperature : 10 seconds or less<br>Time at temperature of 220°C or higher : 60 seconds or less<br>Preheating time at 120 to 180°C : 120±30 seconds<br>Maximum number of reflow processes : 3 times<br>Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below | IR260            |
| Wave Soldering   | Peak temperature (molten solder temperature) : 260°C or below<br>Time at peak temperature : 10 seconds or less<br>Preheating temperature (package surface temperature) : 120°C or below<br>Maximum number of flow processes : 1 time<br>Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below  | WS260            |
| Partial Heating  | Peak temperature (terminal temperature) : 350°C or below<br>Soldering time (per side of device) : 3 seconds or less<br>Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below   | HS350            |

**Caution Do not use different soldering methods together (except for partial heating).**